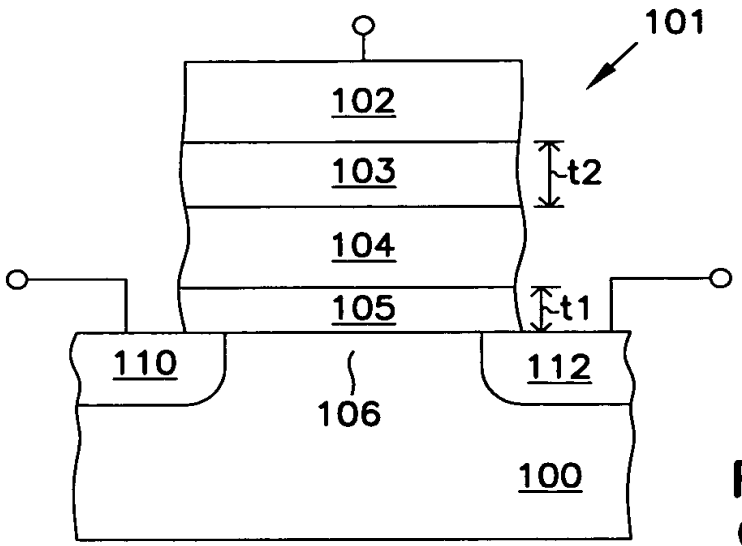

FIG. 1A
(Prior Art)

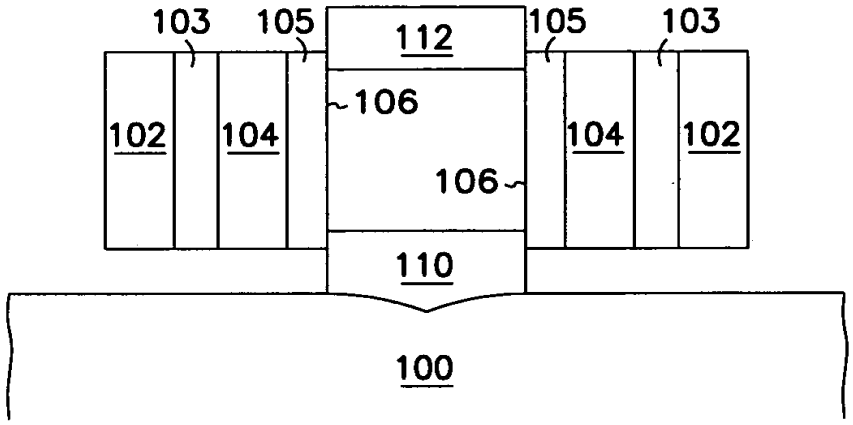

FIG. 1B
(Prior Art)

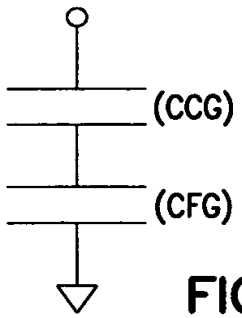

FIG. 1C
(Prior Art)

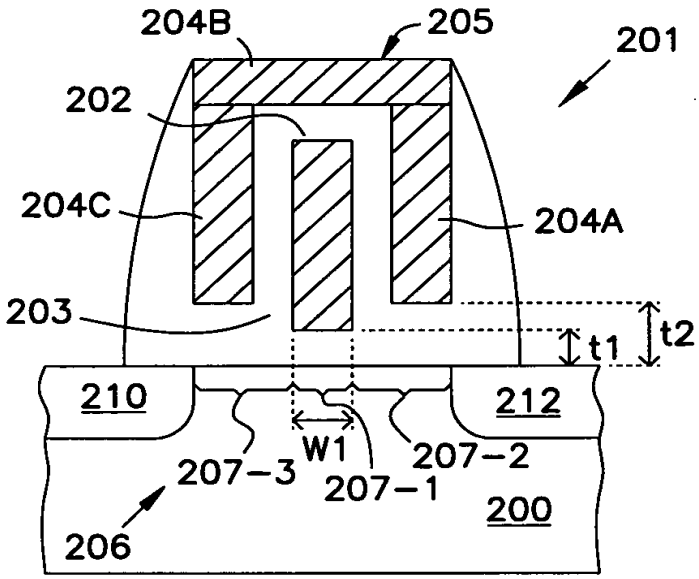

FIG. 2A

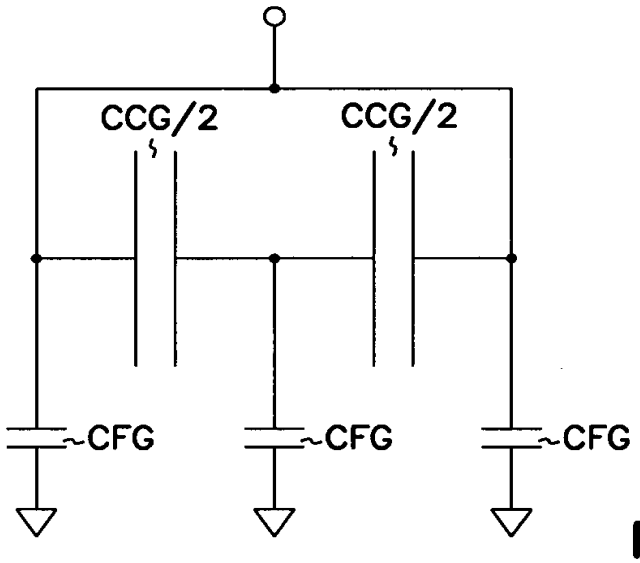

FIG. 2B

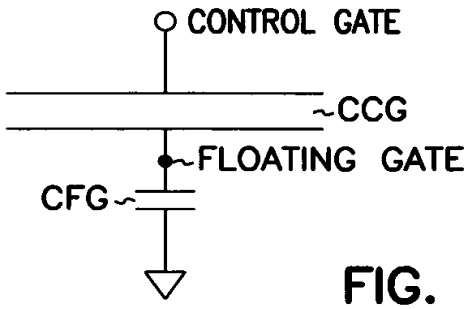

FIG. 2C

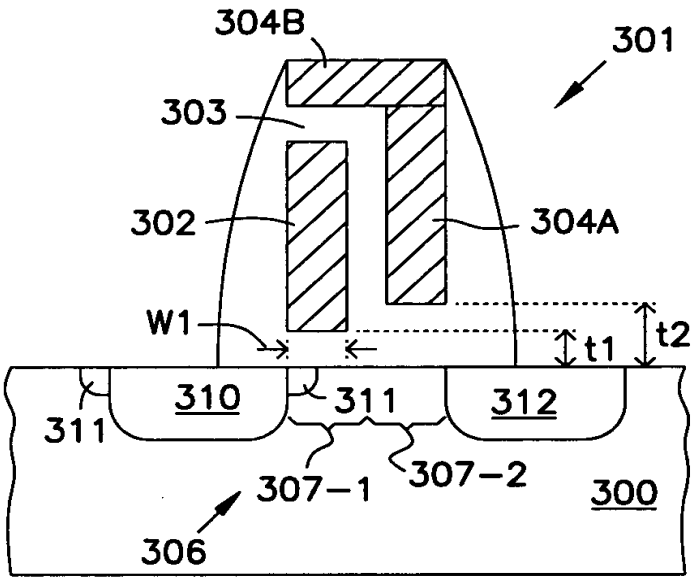

FIG. 3A

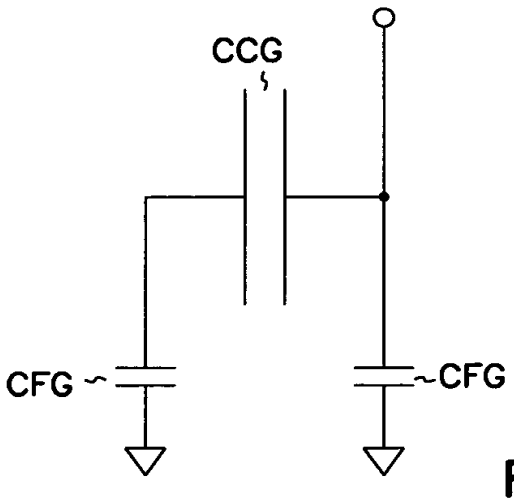

FIG. 3B

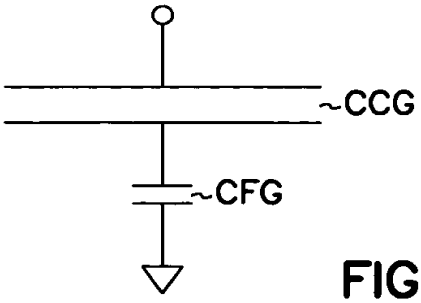

FIG. 3C

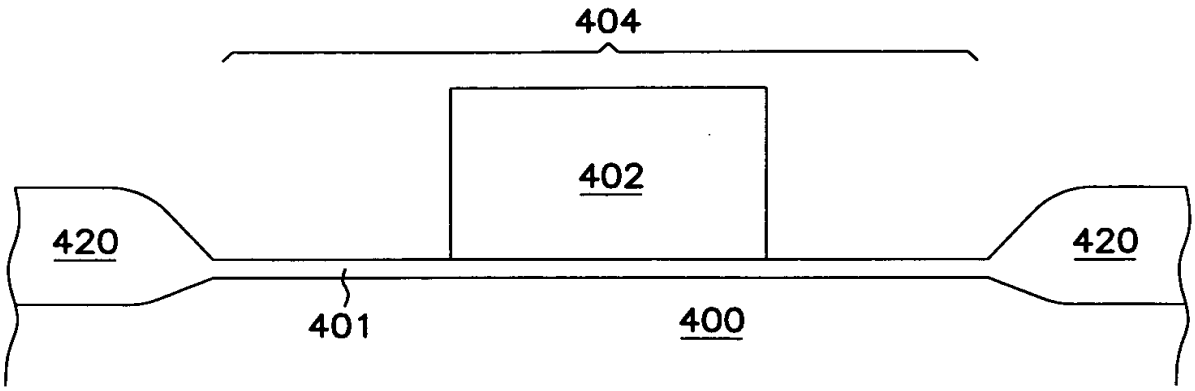

FIG. 4A

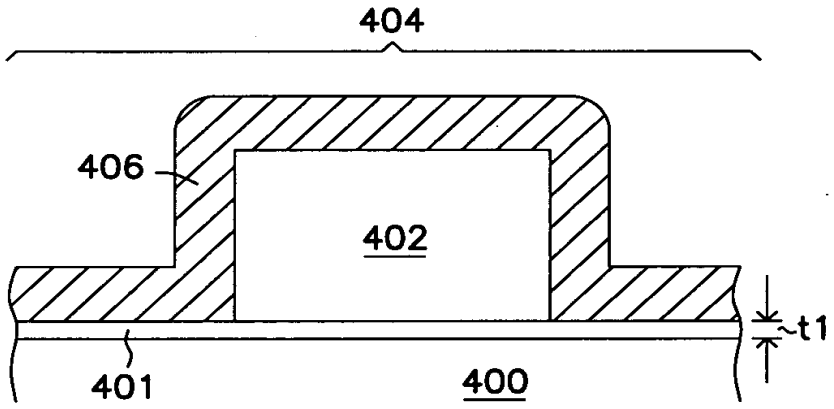

FIG. 4B

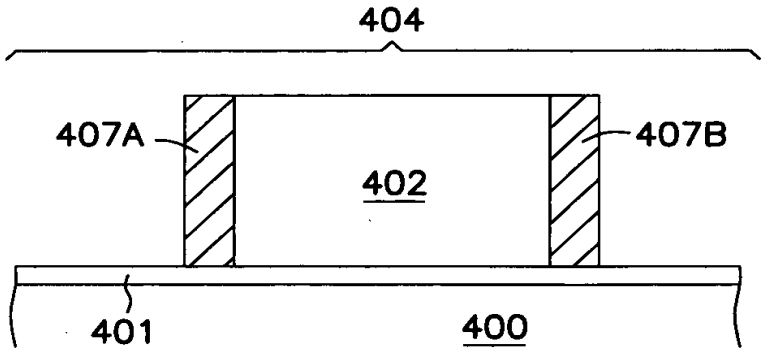

FIG. 4C

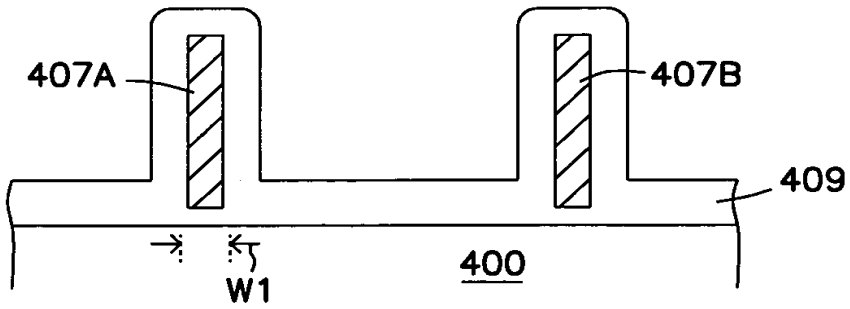

FIG. 4D

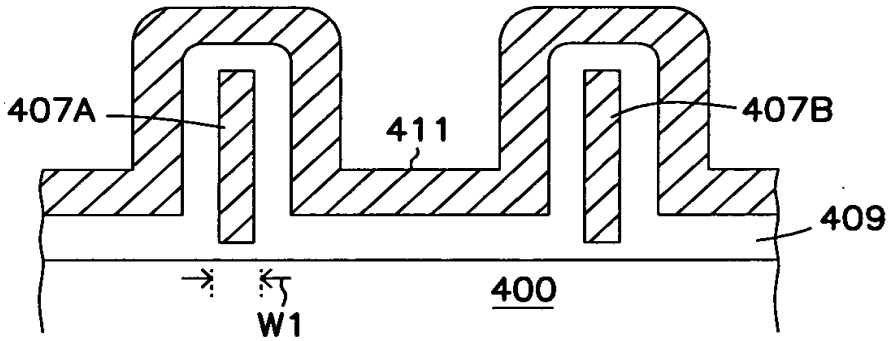

FIG. 4E

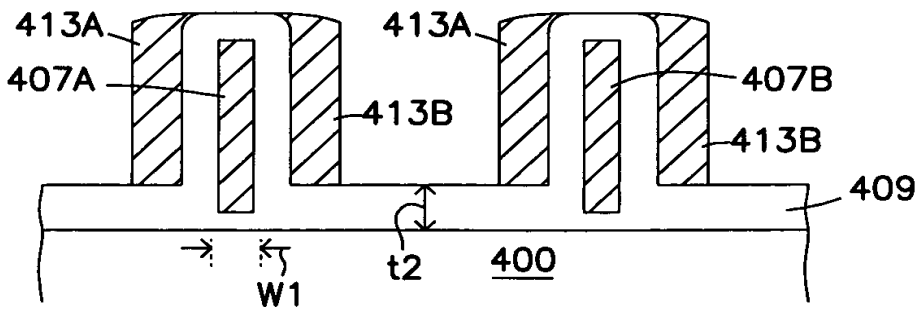

FIG. 4F

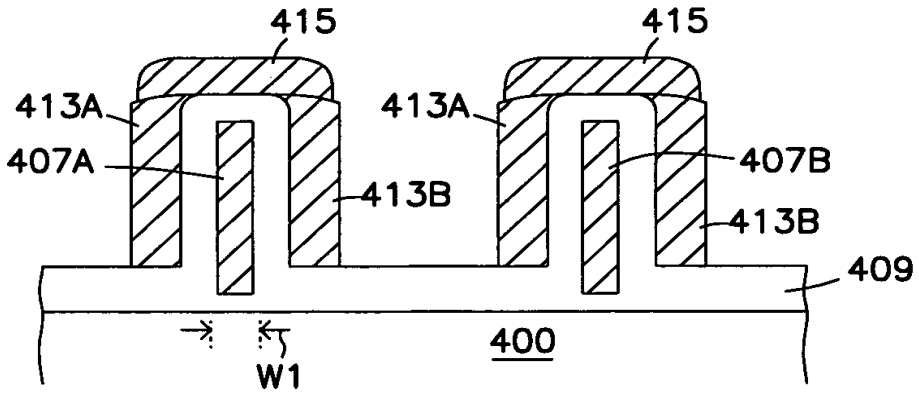

FIG. 4G

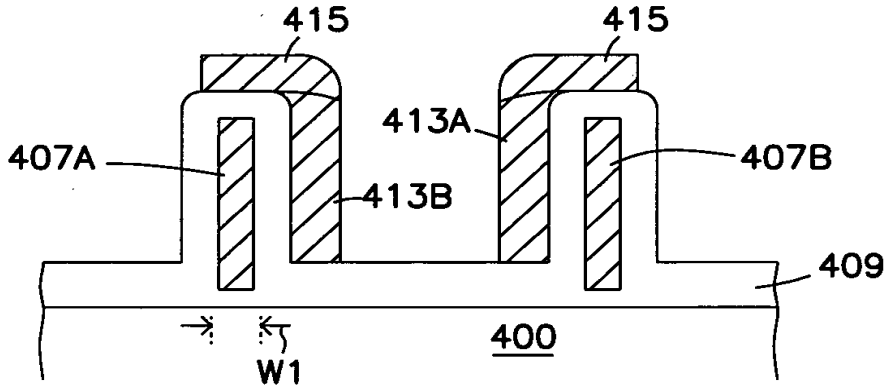

FIG. 4H

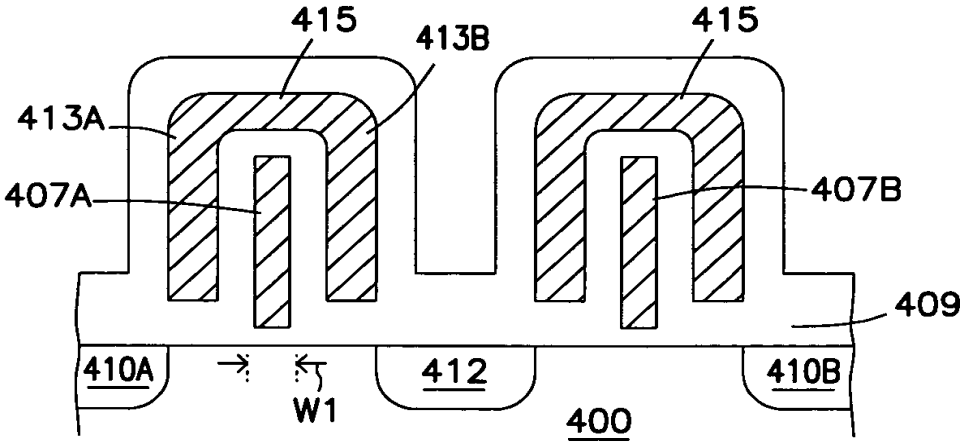

FIG. 4I

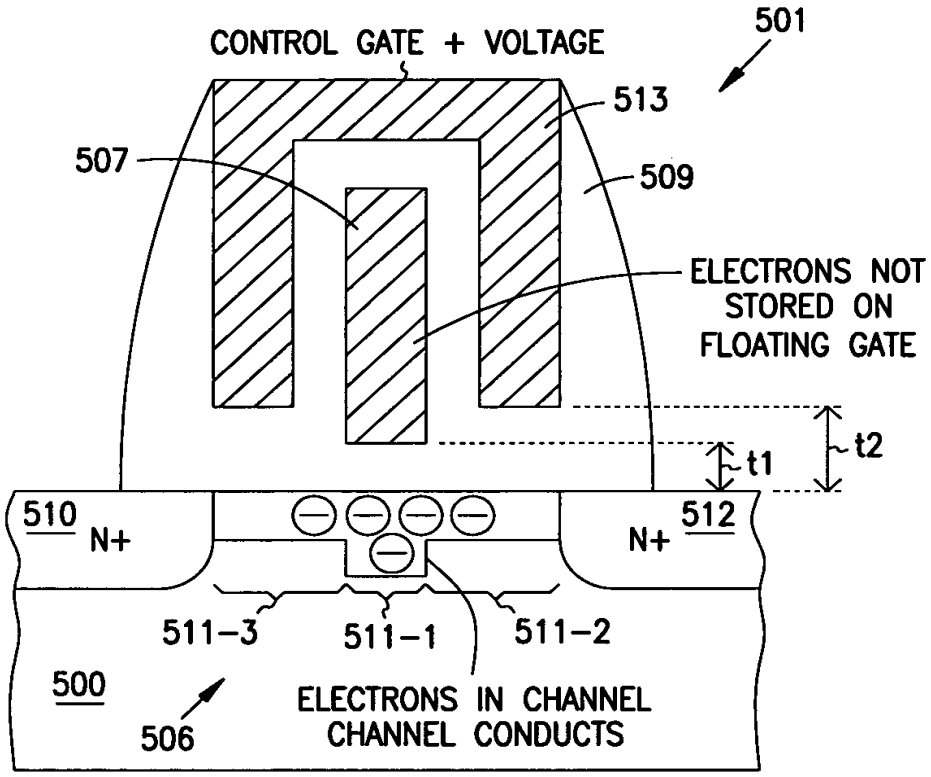
CONTROL GATE + VOLTAGE
501
513
507
509
ELECTRONS NOT
STORED ON
FLOATING GATE
t1
t2
510
N+
512
N+
511-3
511-1
511-2
500
506
ELECTRONS IN CHANNEL
CHANNEL CONDUCTS

FIG. 5A

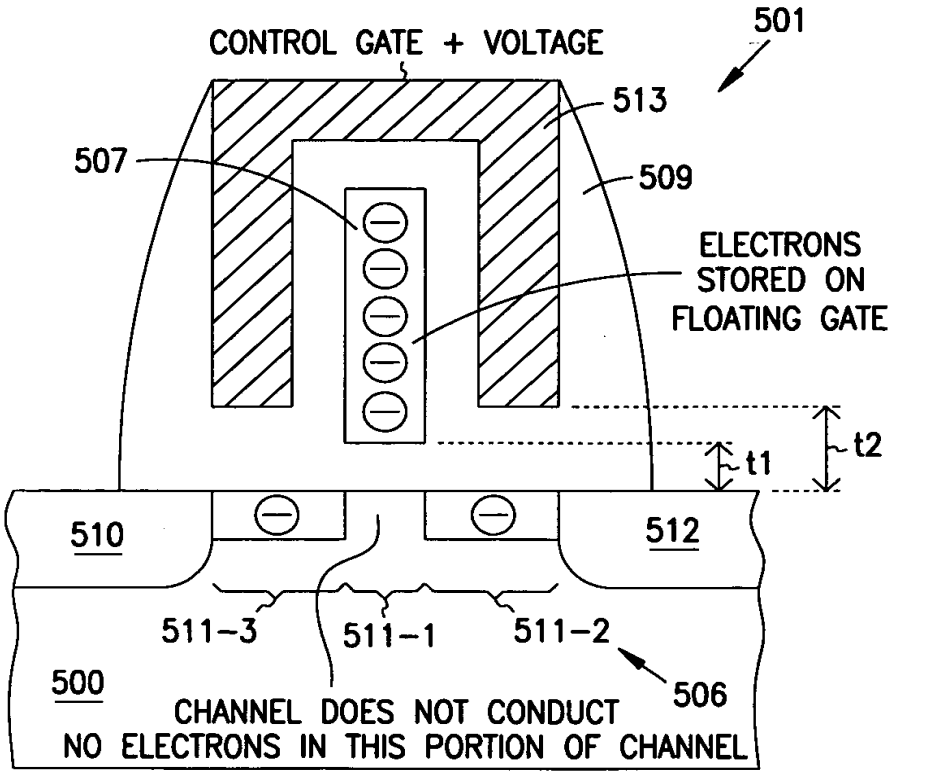
CONTROL GATE + VOLTAGE
501
513
507
509
ELECTRONS
STORED ON
FLOATING GATE
t1
t2
510
512
511-3
511-1
511-2
500
506
CHANNEL DOES NOT CONDUCT
NO ELECTRONS IN THIS PORTION OF CHANNEL

FIG. 5B

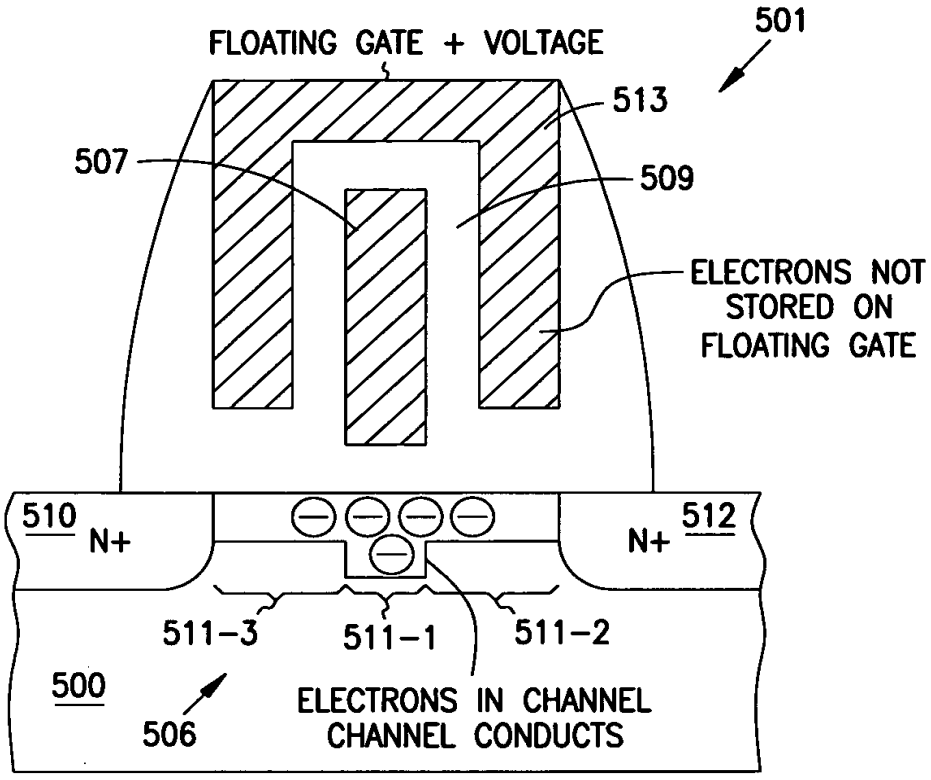
FLOATING GATE + VOLTAGE
501
513
507
509
ELECTRONS NOT
STORED ON
FLOATING GATE
510
N+
512
N+
511-3
511-1
511-2
500
506
ELECTRONS IN CHANNEL
CHANNEL CONDUCTS

FIG. 5C

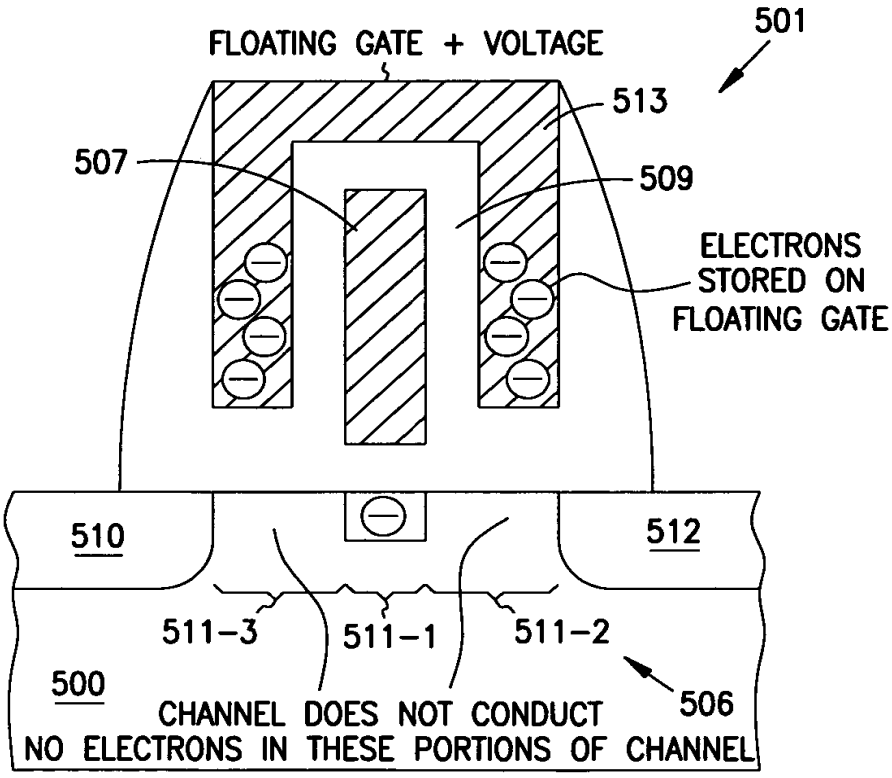
FLOATING GATE + VOLTAGE
501
513
507
509
ELECTRONS
STORED ON
FLOATING GATE
510
512
511-3
511-1
511-2
500
506
CHANNEL DOES NOT CONDUCT
NO ELECTRONS IN THESE PORTIONS OF CHANNEL

FIG. 5D

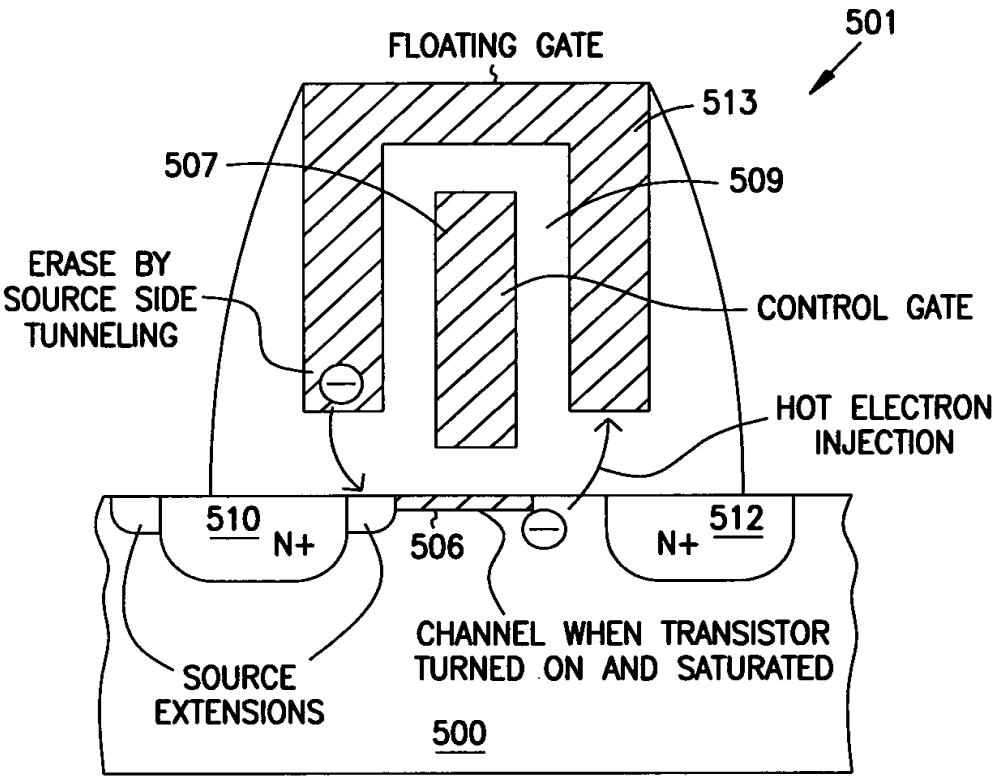
501
FLOATING GATE
513
507
509
ERASE BY
SOURCE SIDE
TUNNELING
CONTROL GATE
HOT ELECTRON
INJECTION
510
N+
506
N+
512
CHANNEL WHEN TRANSISTOR
TURNED ON AND SATURATED
SOURCE
EXTENSIONS
500

FIG. 5E

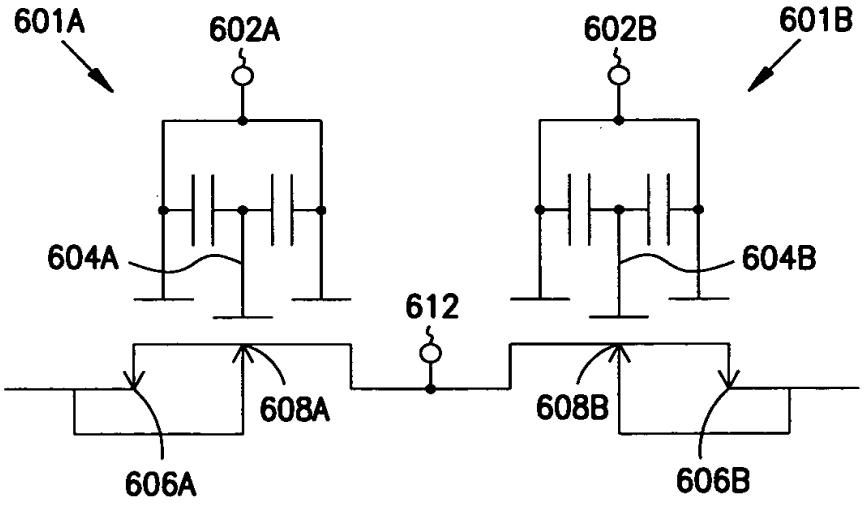
601A
602A
602B
601B
604A
604B
612
608A
608B
606A
606B

FIG. 6

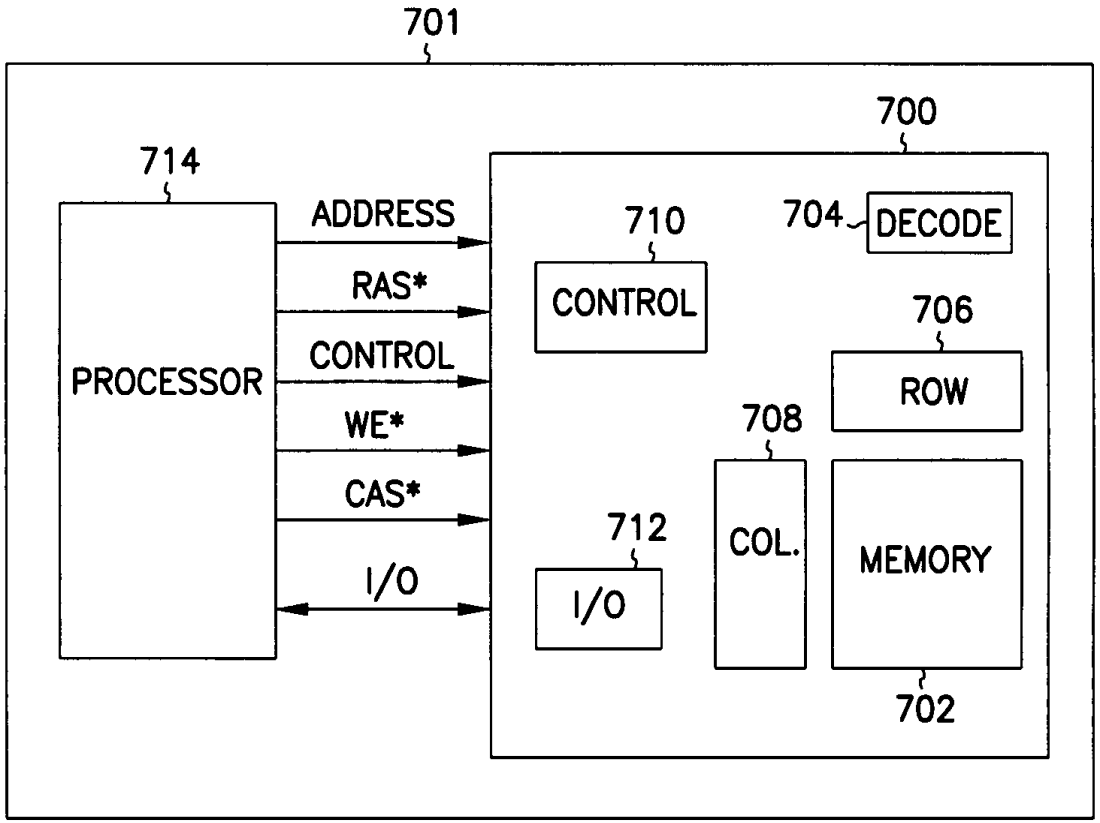

FIG. 7

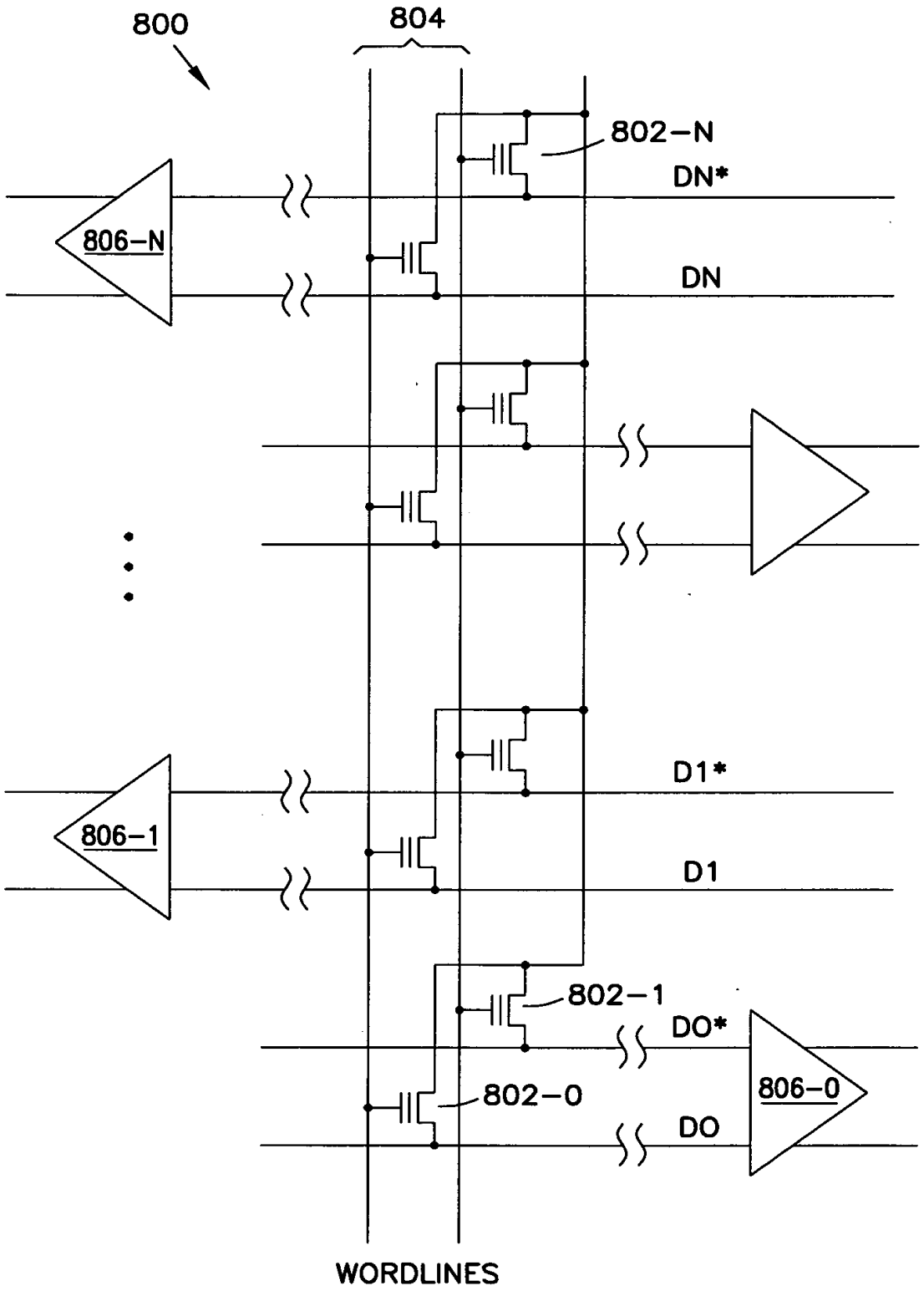
800
804
802-N
DN*
806-N
DN
D1*
806-1
D1
802-1
DO*
802-0
806-0
DO
WORDLINES

FIG. 8